What Is Claimed Is:

1. A method of fabricating a liquid crystal display device having first and second substrates, the method comprising the steps of:

forming a gate line on the first substrate;

sequentially forming a first insulating layer, an amorphous silicon layer, and a metal layer on the first substrate;

patterning the metal layer to form a data line;

forming a second insulating layer on the data line;

patterning the second insulating layer and the amorphous silicon layer to form a passivation layer and an active layer, respectively;

forming a pixel electrode at a pixel region defined by the gate and data lines;

assembling the first substrate and the second substrate having a black matrix thereon, wherein the black matrix vertically overlaps at least one boundary line defined by different exposures during step-and-repeat exposure processes; and

forming a liquid crystal layer between the first and second substrates.

2. The method of claim 1, wherein the boundary line is disposed over the gate line and the data line.

3. A method of fabricating a liquid crystal display device having first and second substrates, comprising:

forming a gate line on the first substrate;

forming a gate insulating layer on the first substrate including the gate line;

forming an amorphous silicon layer on the gate insulating layer;

forming a data line on the amorphous silicon layer;

forming an insulating layer on the amorphous silicon layer including the data line;

forming a photoresist layer having first, second, and third portions on the insulating layer, wherein the first portion has a thickness greater than the second portion, and the third portion exposes a portion of the insulating layer;

selectively removing the insulating layer and the amorphous layer to form a passivation layer on the data line and an active layer below the data line;

forming a pixel electrode on the gate insulating

layer;

forming a black matrix over the second substrate; and

assembling the first and second substrates to substantially overlap at least one boundary line and the black matrix in a vertical direction, wherein the boundary lines is defined during step-and-repeat exposures at different times.

4. The method of claim 3, wherein the pixel electrode has a stitch line therein.

5. The method of claim 3, wherein the gate insulating layer has a stitch line therein.

6. The method of claim 3, wherein the exposed portion of the insulating layer vertically overlaps the gate line.

7. A liquid crystal display device comprising:

first and second substrates facing into each other;

a gate line on the first substrate;

a gate insulating layer on the first substrate including the gate line;

an active layer on the gate insulating layer;

a data line over the active layer;

a passivation layer on the data line;

a pixel electrode on the gate insulating layer and having a stitch line therein;

a black matrix over the second substrate, wherein the stitch line in the pixel electrode substantially overlaps the black matrix in a vertical direction.

8. A liquid crystal display device comprising:

first and second substrates facing into each other;

a gate line on an inner surface of the first substrate;

a first insulating layer on the gate line;

a silicon layer on the first insulating layer;

a data line on the silicon layer, the data line crossing the gate line;

a second insulating layer on the data line, the second insulating layer having the same shape as the silicon layer;

a pixel electrode at a pixel region defined by the gate and data lines;

a black matrix on an inner surface of the second

substrate;

a common electrode on the black matrix; and

a liquid crystal layer between the first and second substrates, wherein at least one stitch line is formed in the gate insulating layer during a step-and-repeat exposure for forming the second insulating layer, and the black matrix substantially overlaps the stitch line in a vertical direction.